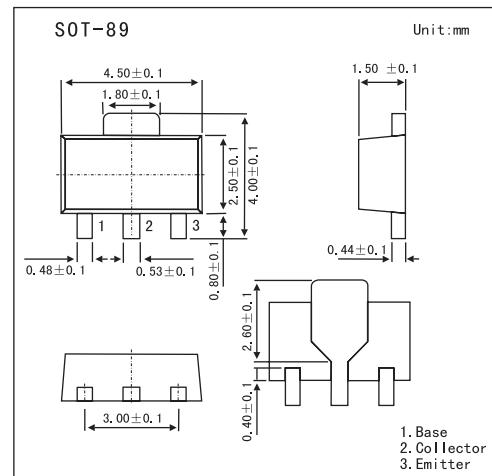


PXT222A

■ Features

- High current (max. 600 mA)
- Low voltage (max. 40 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation	P _{tot}		
* 1		0.5	
* 2		0.8	
* 3		1.1	
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient	R _{th(j-a)}		K/W
* 1		250	
* 2		156	
* 3		113	
Thermal resistance from junction to soldering point	R _{th(j-s)}	30	K/W

*1 Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard - footprint.

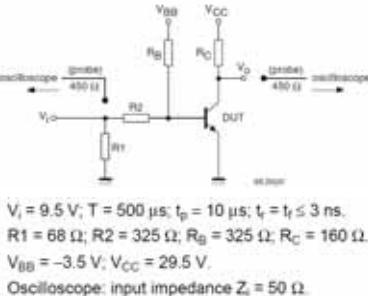
*2 Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm².

*3 Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm².

PXT222A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	I _E = 0; V _{CB} = 60 V			10	nA
		I _E = 0; V _{CB} = 60 V; T _J = 125 °C			10	µA
Emitter cutoff current	I _{EO}	I _C = 0; V _{EB} = 5 V			10	nA
DC current gain	h _{FE}	I _C = 0.1 mA; V _{CE} = 10V	35			
		I _C = 1 mA; V _{CE} = 10 V	50			
		I _C = 10 mA; V _{CE} = 10 V	75			
		I _C = 10 mA; V _C = 10 V; T _J = -55 °C	35			
		I _C = 150 mA; V _{CE} = 1 V	50			
		V _{CE} = 10 V, I _C = 150 mA	100		300	
		I _C = 500 mA; V _{CE} = 10 V	40			
collector-emitter saturation voltage	V _{CEsat}	I _C = 150 mA; I _B = 15 mA			300	mV
		I _C = 500 mA; I _B = 50 mA			1	V
base-emitter saturation voltage	V _{BEsat}	I _C = 150 mA; I _B = 15 mA	0.6		1.2	V
		I _C = 500 mA; I _B = 50 mA			2	V
Collector capacitance	C _c	I _E = I _E = 0; V _{CB} = 10 V; f = 1 MHz			8	pF
Emitter capacitance	C _e	I _C = I _C = 0; V _{EB} = 500 mV; f = 1 MHz			25	pF
Transition frequency	f _T	I _C = 20 mA; V _{CE} = 10 V; f = 100 MHz	300			MHz
Noise figure	F	I _C = 200 µA; V _{CE} = 5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz			4	dB
Turn-on time	t _{on}	I _{Con} = 150 mA; I _{Bon} = 15 mA; I _{Boff} = -15 mA			35	ns
Delay time	t _d				15	ns
Rise time	t _r				20	ns
Turn-off time	t _{off}				250	ns
Storage time	t _s				200	ns
Fall time	t _f				60	ns



■ Marking

Marking	1P
---------	----